

2SC2188

Silicon NPN epitaxial planar type

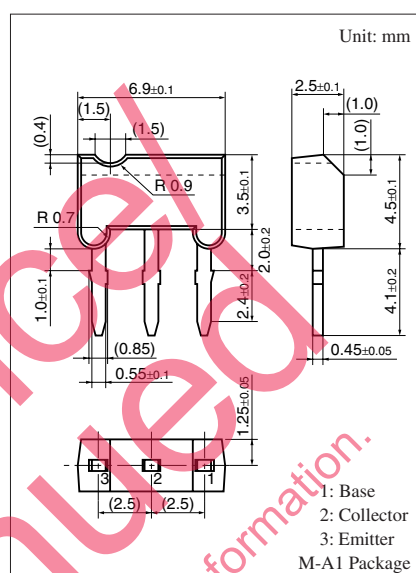
For intermediate frequency amplification of TV image

■ Features

- High transition frequency f_T
- Satisfactory linearity of forward current transfer ratio h_{FE}
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

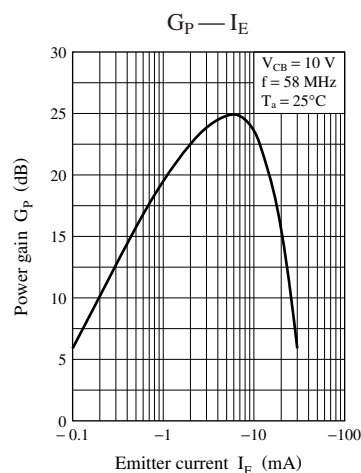
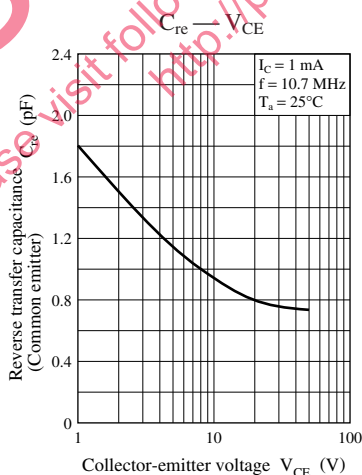
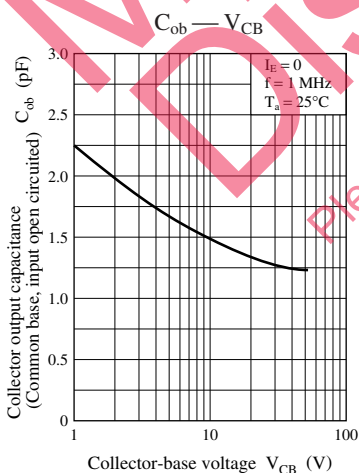
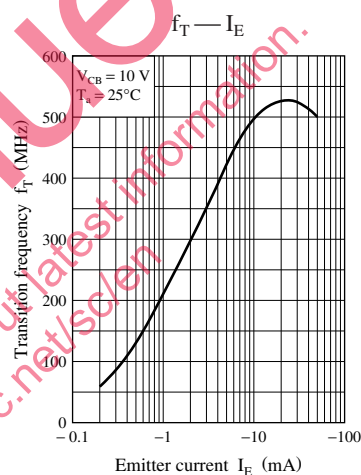
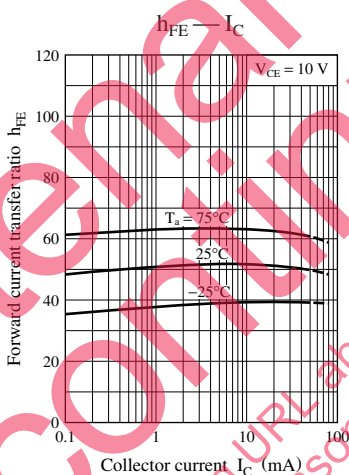
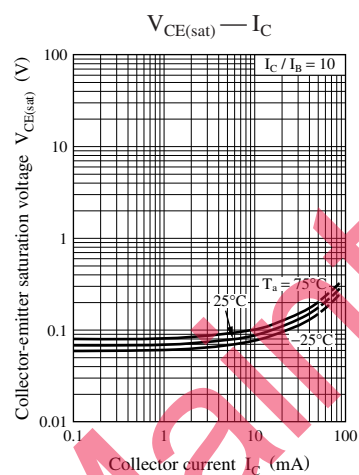
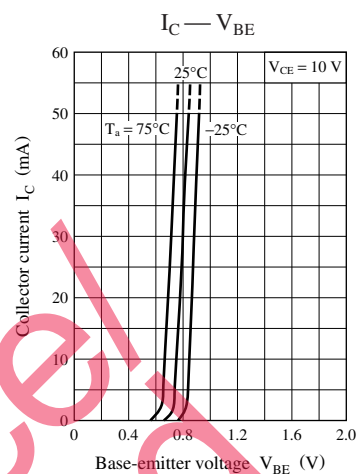
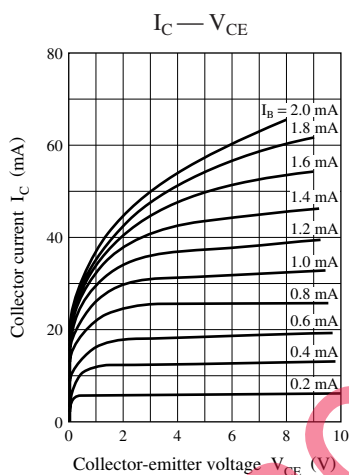
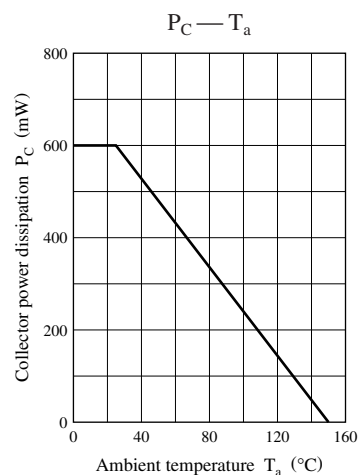
| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 45 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 35 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 4 | V |
| Collector current | I_C | 50 | mA |
| Collector power dissipation | P_C | 600 | mW |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---------------|--|-----|-----|-----|---------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}$, $I_E = 0$ | 45 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 1 \text{ mA}$, $I_B = 0$ | 35 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}$, $I_C = 0$ | 4 | | | V |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 20 \text{ V}$, $I_B = 0$ | | | 10 | μA |
| Forward current transfer ratio | h_{FE} | $V_{CB} = 10 \text{ V}$, $I_E = -10 \text{ mA}$ | 20 | 50 | 100 | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 20 \text{ mA}$, $I_B = 2 \text{ mA}$ | | | 0.5 | V |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}$, $I_E = -10 \text{ mA}$, $f = 100 \text{ MHz}$ | 300 | 500 | | MHz |
| Reverse transfer capacitance (Common emitter) | C_{re} | $V_{CB} = 10 \text{ V}$, $I_E = -1 \text{ mA}$, $f = 10.7 \text{ MHz}$ | | | 1.5 | pF |
| Power gain | G_p | $V_{CB} = 10 \text{ V}$, $I_E = -10 \text{ mA}$, $f = 58 \text{ MHz}$ | | 18 | | dB |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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